

Docket: TSMC 02 - 0015

S/N: TBD

To: Commissioner of Patents and Trademarks  
P.O. Box 1450  
Alexandria, VA 22313-1450

From: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject:

Continuation Application Based upon Application  
Serial No.: 10/282,387 Filed: 10/29/02

Inventor: Tuo-Hung Hou

## Title: A Novel Dual Gate Dielectric Scheme: SiON for High Performance Devices and High K for Low Power Devices

Group Art Unit: TBD Examiner: TBD  
Attorney Docket: TSMC 02 – 0015

## PRELIMINARY AMENDMENT

Dear Sir:

As a Preliminary Amendment for the above-identified Continuation  
Application filed concurrently herewith, please consider the following remarks.

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on Oct 6, 2003

**Signature**

**Signature** 

Stephen B. Ackerman, Reg. No. 37,761

Date: Oct. 6, 2003